

Silicon Diodes

General Purpose and Switching Diodes (MiniMELF Glass Package)

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_o	Power Dissipation at 25 °C	Junction Temperature T_j	Forward Voltage Drop V_F	Reverse Current I_R		Reverse Recovery Time			
						at I_F		at V_R		t_{rr} ns	Conditions
						Volts	mA	max. mW	max. °C		
BAV100	60	200	500	175	1.0	100	100	50	max. 50	$I_F = I_R = 30$ mA, $R_L = 100$ Ω to $I_R = 3$ mA	
BAV101	120	200	500	175	1.0	100	100	100	max. 50	$I_F = I_R = 30$ mA, $R_L = 100$ Ω to $I_R = 3$ mA	
BAV102	200	200	500	175	1.0	100	100	150	max. 50	$I_F = I_R = 30$ mA, $R_L = 100$ Ω to $I_R = 3$ mA	
BAV103	250	200	500	175	1.0	100	100	200	max. 50	$I_F = I_R = 30$ mA, $R_L = 100$ Ω to $I_R = 3$ mA	
LL4148	100	150	500	175	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
LL4149	100	150	500	175	1.0	10	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
LL4150	50	200	500	175	1.0	200	100	50	max. 4.0	$I_F = I_R = 10$ to 200 mA, to 0.1 I_F	
LL4151	75	150	500	175	1.0	50	50	50	max. 2.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
LL4448	100	150	500	175	1.0	100	25	20	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
LL4454	75	150	500	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10$ mA, to $I_R = 1$ mA	

Fast Switching Diodes (SOT23 Plastic Package)

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_o	Power Dissipation at 25 °C	Junction Temperature T_j	Forward Voltage Drop V_F	Reverse Current I_R		Reverse Recovery Time			
						at I_F		at V_R		t_{rr} ns	Conditions
						Volts	mA	max. mW	max. °C		
BAL99	70	150	350	150	1.0	50	2.5 μ A	70	max. 6.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAS16	75	150	350	150	1.0	50	1 μ A	75	max. 6.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAS19	120	200	250	150	1.0	100	100	100	max. 50	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAS20	200	200	250	150	1.0	100	100	150	max. 50	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAS21	250	200	250	150	1.0	100	100	200	max. 50	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
IMBD4148	75	150	350	150	1.0	10	2.5 μ A	70	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
IMBD4444	75	150	350	150	1.0	100	2.5 μ A	70	max. 4.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	

The pin configuration is the following:

BAL99, 1 = Anode, 3 = Katode; BAS16, 1 = Katode, 2 = Anode; BAS19, BAS20, BAS21, 1 = Katode, 2 = Anode; IMBD4148, IMBD4444, 1 = Katode, 2 = Anode

Fast Switching Dual Diodes (SOT23 Plastic Package) The same values apply for both diodes.

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_o	Power Dissipation at 25 °C	Junction Temperature T_j	Forward Voltage Drop V_F	Reverse Current I_R		Reverse Recovery Time			
						at I_F		at V_R		t_{rr} ns	Conditions
						Volts	mA	max. mW	max. °C		
BAV70	70	250	350	150	1.0	50	2.5 μ A	70	max. 6.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAV99	70	250	350	150	1.0	50	2.5 μ A	70	max. 6.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	
BAW56	70	250	350	150	1.0	50	2.5 μ A	70	max. 6.0	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω , to $I_R = 1$ mA	

The pin configuration is the following:

BAV70, 1 = Katode, Katode, 2 = Anode, 3 = Anode; BAV99, 1 = Anode, Katode, 2 = Anode, 3 = Katode; BAW56, 1 = Anode, Anode, 2 = Katode, 3 = Katode